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(54) Title: EPITAXIAL SILICON WAFERS SUBSTANTIALLY FREE OF GROWN-IN DEFECTS

(57) Abstract

The present invention is directed to a set of epitaxial silicon wafers assembled in a wafer cassette, boat or other wafer carrier. Each wafer comprises a single crystal silicon substrate having an axially symmetric region in which silicon self-interstitials are the predominant intrinsic point defect and which is substantially free of agglomerated defects, and an epitaxial layer which is deposited upon a surface of the substrate and which is substantially free of grown-in defects caused by the presence of agglomerated silicon self-interstitial defects on the substrate surface upon which the epitaxial layer is deposited.

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